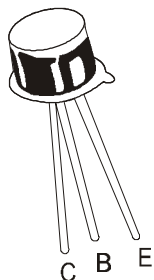


## NPN SILICON PLANAR TRANSISTORS

**2N930**  
**2N930A**



**TO-18**  
**Metal Can Package**

### Low Noise Transistors

#### ABSOLUTE MAXIMUM RATINGS

DESCRIPTION	SYMBOL	2N930	2N930A	UNIT
Collector Emitter Voltage	$V_{CEO}$	45	60	V
Collector Base Voltage	$V_{CBO}$	45	60	V
Emitter Base Voltage	$V_{EBO}$	5	6	V
Collector Current Continuous	$I_C$	30		mA
Power Dissipation @ $T_a=25^\circ\text{C}$ Derate Above $25^\circ\text{C}$	$P_D$	300		mW
		1.72		mW/°C
Power Dissipation @ $T_c=25^\circ\text{C}$ Derate Above $25^\circ\text{C}$	$P_D$	600		mW
		3.42		mW/°C
Operating And Storage Junction Temperature Range	$T_j, T_{stg}$	- 65 to +200		°C

#### THERMAL CHARACTERISTICS

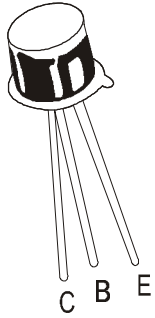
Junction to Ambient in free air	$R_{th(j-a)}$	583	°C/W
Junction to Case	$R_{th(j-c)}$	292	°C/W

#### ELECTRICAL CHARACTERISTICS ( $T_a=25^\circ\text{C}$ unless specified otherwise)

DESCRIPTION	SYMBOL	TEST CONDITION	2N930	2N930A	UNIT
Collector Emitter Voltage	$*V_{CEO}$	$I_C=10\text{mA}, I_B=0$	>45	>60	V
Collector Base Voltage	$V_{CBO}$	$I_C=10\mu\text{A}, I_E=0$	>45	>60	V
Emitter Base Voltage	$V_{EBO}$	$I_E=10\mu\text{A}, I_C=0$	>5	>6	V
Collector Cut Off Current	$I_{CBO}$	$V_{CB}=45\text{V}, I_E=0$	<10	<2	nA
Collector Cut Off Current	$I_{CEO}$	$V_{CE}=5\text{V}, I_B=0$	<2	<2	nA
Emitter Cut Off Current	$I_{EBO}$	$V_{EB}=5\text{V}, I_C=0$	<10	<2	nA
Collector Cut Off Current	$I_{CES}$	$V_{CE}=45\text{V}, V_{BE}=0$	<10	<2	nA
		$V_{CE}=45\text{V}, V_{BE}=0, T_a=170^\circ\text{C}$	<10	<2	$\mu\text{A}$
Collector Emitter Saturation Voltage	$*V_{CE(sat)}$	$I_C=10\text{mA}, I_B=0.5\text{mA}$	<1.0	<0.5	V
Base Emitter Saturation Voltage	$*V_{BE(sat)}$	$I_C=10\text{mA}, I_B=0.5\text{mA}$	0.7 - 0.9	0.7 - 0.9	V
DC Current Gain	$h_{FE}$	$I_C=1\mu\text{A}, V_{CE}=5\text{V}$		>60	
		$I_C=10\mu\text{A}, V_{CE}=5\text{V}$	100-300	100-300	
		$I_C=10\mu\text{A}, V_{CE}=5\text{V}, T_a=-55^\circ\text{C}$	>20	>30	
		$I_C=500\mu\text{A}, V_{CE}=5\text{V}$	>150		
		$*I_C=10\text{mA}, V_{CE}=5\text{V}$	<600	<600	

\*Pulse Test: Pulse width  $\leq 300\text{ms}$ , Duty cycle  $\leq 2\%$

# NPN SILICON PLANAR TRANSISTORS



**2N930**  
**2N930A**

**TO-18**  
**Metal Can Package**

## ELECTRICAL CHARACTERISTICS ( $T_a=25^\circ\text{C}$ unless specified otherwise)

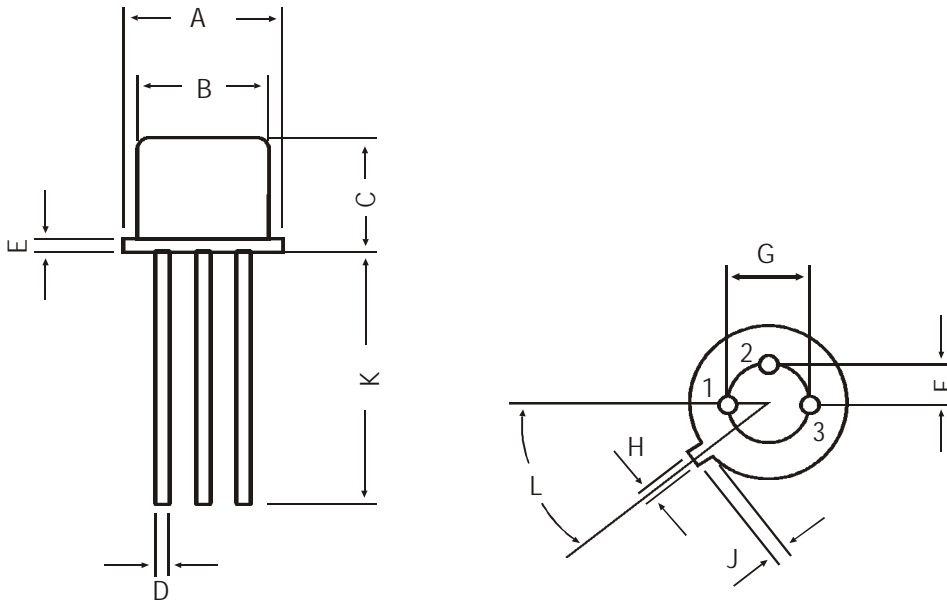
### DYNAMIC CHARACTERISTICS

DESCRIPTION	SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNIT
Transition frequency	$f_T$	$I_C=500\mu\text{A}, V_{CE}=5\text{V}, f=30\text{MHz}$ <b>2N930</b> <b>2N930A</b>	30 45			MHz MHz
Output Capacitance	$C_{ob}$	$V_{CB}=5\text{V}, I_E=0, f=1\text{MHz}$ <b>2N930</b> <b>2N930A</b>			8 6	pF pF
Input Impedance	$h_{ib}$	$I_C=1\text{mA}, V_{CB}=5\text{V}, f=1\text{kHz}$	25		32	$\Omega$
Voltage Feedback Ratio	$h_{rb}$	$I_C=1\text{mA}, V_{CB}=5\text{V}, f=1\text{kHz}$			600	$\times 10^{-6}$
Small Signal Current Gain	$h_{fe}$	$I_C=1\text{mA}, V_{CE}=5\text{V}, f=1\text{kHz}$	150		600	
Output Admittance	$h_{ob}$	$I_C=1\text{mA}, V_{CB}=5\text{V}, f=1\text{kHz}$			1	$\mu\text{S}$
Noise Figure	NF	$I_C=10\mu\text{A}, V_{CE}=5\text{V}, R_g=10\text{k}\Omega,$ $f=10\text{Hz to } 15.7\text{kHz}$			3	dB

**2N930**  
**2N930A**

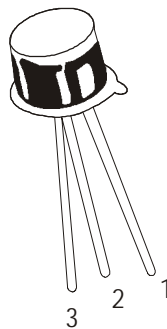
**TO-18**  
**Metal Can Package**

**TO-18 Metal Can Package**



All dimensions in mm.

DIM	MIN	MAX
A	5.24	5.84
B	4.52	4.97
C	4.31	5.33
D	0.40	0.53
E	—	0.76
F	—	1.27
G	—	2.97
H	0.91	1.17
J	0.71	1.21
K	12.70	—
L	45 DEG	



**PIN CONFIGURATION**

1. EMITTER
2. BASE
3. COLLECTOR

**Packing Detail**

PACKAGE	STANDARD PACK		INNER CARTON BOX		OUTER CARTON BOX		
	Details	Net Weight/Qty	Size	Qty	Size	Qty	Gr Wt
TO-18	1K/polybag	350 gm/1K pcs	3" x 7.5" x 7.5"	5K	17" x 15" x 13.5"	80K	34 kgs

### **Disclaimer**

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